TSHG5510

RoHS

COMPLIANT **GREEN**

(5-2008)**



Vishay Semiconductors

High Speed Infrared Emitting Diode, 830 nm, **GaAlAs Double Hetero**



TSHG5510 is an infrared, 830 nm emitting diode in GaAlAs

double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

- · Package type: leaded
- Package form: T-1¾
- Dimensions (in mm): Ø 5
- · Leads with stand-off
- Peak wavelength: $\lambda_p = 830 \text{ nm}$
- · High reliability
- · High radiant power
- · High radiant intensity
- Angle of half intensity: $\varphi = \pm 38^{\circ}$
- · Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: f_c = 24 MHz
- · Good spectral matching to Si photodetectors
- · Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras (illumination)
- · High speed IR data transmission

PRODUCT SUMMARY

DESCRIPTION

COMPONENT	l _e (mW/sr)	φ (deg)	λ _p (nm)	t _r (ns)
TSHG5510	32	± 38	830	15

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATI	ON		
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHG5510	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	5	V
Forward current		I _F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA
Surge forward current	t _p = 100 μs	I _{FSM}	1	А
Power dissipation		Pv	180	mW
Junction temperature		Tj	100	°C
Operating temperature range		T _{amb}	- 40 to + 85	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	$t \leq 5 \mbox{ s, } 2 \mbox{ mm}$ from case	T _{sd}	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R _{thJA}	230	K/W

1 For technical questions, contact: emittertechsupport@vishay.com Document Number: 81887

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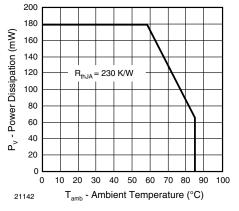


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

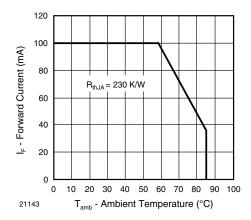


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F	1.3	1.45	1.7	V
	I _F = 450 mA, t _p = 100 μs	V _F	1.5	1.75	2.1	V
	I _F = 1 A, t _p = 100 μs	V _F		2.1		V
Temperature coefficient of V_F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μA
Junction capacitance	$V_{R} = 0 V, f = 1 MHz, E = 0$	Cj		110		pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	I _e	18	32	54	mW/sr
	I _F = 1 A, t _p = 100 μs	l _e		320		mW/sr
Radiant power	I _F = 100 mA, t _p = 20 ms	φ _e		55		mW
Temperature coefficient of ϕ_{e}	l _F = 100 mA	TKφ _e		- 0.35		%/K
Angle of half intensity		φ		± 38		deg
Peak wavelength	l _F = 100 mA	λρ		830		nm
Spectral bandwidth	l _F = 100 mA	Δλ		55		nm
Temperature coefficient of λ_p	l _F = 100 mA	TKλ _p		0.25		nm/K
Rise time	l _F = 100 mA	t _r		15		ns
Fall time	l _F = 100 mA	t _f		15		ns
Cut-off frequency	$I_{DC} = 70 \text{ mA}, I_{AC} = 30 \text{ mA pp}$	f _c		24		MHz

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BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

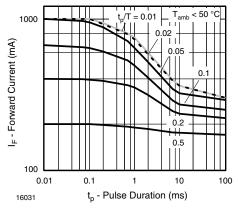


Fig. 3 - Pulse Forward Current vs. Pulse Duration

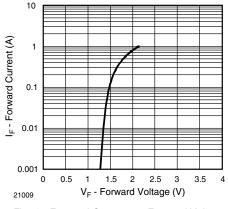


Fig. 4 - Forward Current vs. Forward Voltage

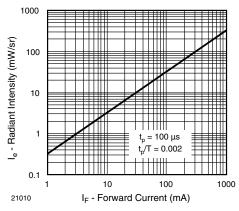


Fig. 5 - Radiant Intensity vs. Forward Current

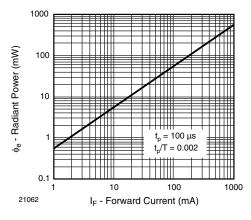
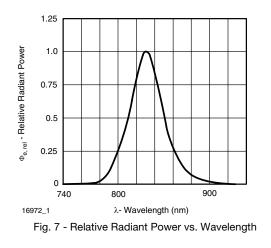
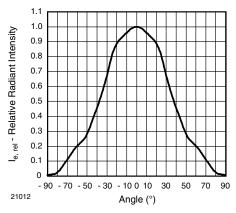


Fig. 6 - Radiant Power vs. Forward Current





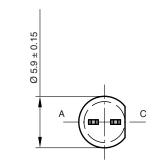


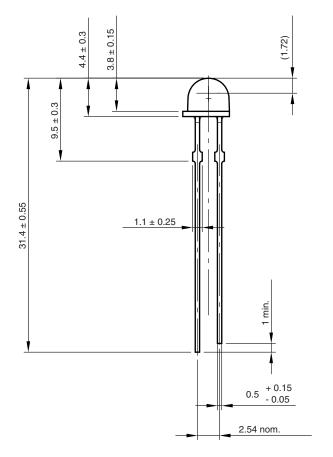
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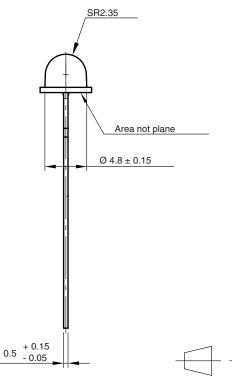
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PACKAGE DIMENSIONS in millimeters







technical drawings according to DIN specifications

Drawing-No.: 6.544-5390.01-4 Issue: 2; 19.05.09 20796

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